PZT751

PNP Silicon Planar Epitaxial Transistor

This PNP Silicon Epitaxial transistor is designed for use in industrial and consumer applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

Features

- High Current
- The SOT-223 Package can be soldered using wave or reflow.
- SOT-223 Package Ensures Level Mounting, Resulting in Improved Thermal Conduction, and Allows Visual Inspection of Soldered Joints. The Formed Leads Absorb Thermal Stress During Soldering, Eliminating the Possibility of Damage to the Die
- NPN Complement is PZT651T1
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	2.0	Adc
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	0.8 6.4	W mW/°C
Storage Temperature Range	T _{stg}	-65 to 150	°C
Junction Temperature	TJ	150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance from Junction-to- Ambient in Free Air	$R_{\theta JA}$	156	°C/W
Maximum Temperature for Soldering Purposes	TL	260	°C
Time in Solder Bath		10	Sec

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



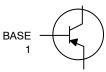
ON Semiconductor®

http://onsemi.com

SOT-223 PACKAGE HIGH CURRENT PNP SILICON TRANSISTOR SURFACE MOUNT

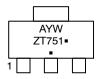






EMITTER 3

MARKING DIAGRAM



A = Assembly Location

Y = Year W = Work Week

(Note: Microdot may be in either location)

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
PZT751T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT751T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

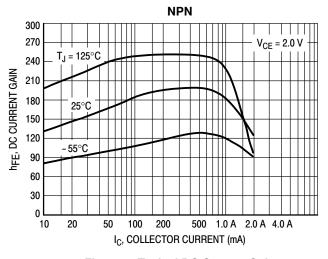
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PZT751

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

ELECTRICAL CHATACTERIOTICS (TA = 25 G unless otherwise noted)				
Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·		•	
Collector–Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _(BR) CEO	60	-	Vdc
Collector–Emitter Breakdown Voltage (I_C = 100 μ Adc, I_E = 0)	V _(BR) CBO	80	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	Vdc
Base-Emitter Cutoff Current (V _{EB} = 4.0 Vdc)	I _{EBO}	_	0.1	μAdc
Collector-Base Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	I _{CBO}	_	100	nAdc
ON CHARACTERISTICS (Note 2)				
DC Current Gain ($I_C = 50 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h _{FE}	75 75 75 40	- - - -	-
Collector–Emitter Saturation Voltages (I_C = 2.0 Adc, I_B = 200 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	V _{CE(sat)}	- -	0.5 0.3	Vdc
Base-Emitter Voltages (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	1.0	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 100 mAdc)	V _{BE(sat)}	-	1.2	Vdc
Current-Gain-Bandwidth (I _C = 50 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	75	-	MHz

^{2.} Pulse Test: Pulse Width \leq 300 $\mu\text{s},$ Duty Cycle = 2.0%.





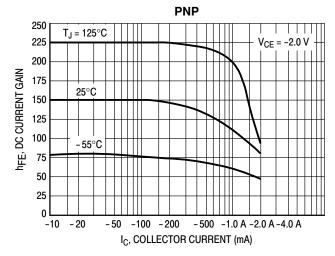


Figure 2. Typical DC Current Gain

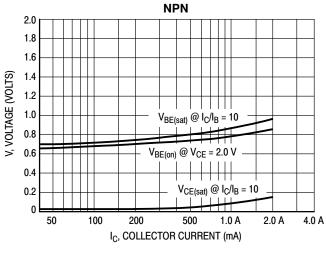


Figure 3. On Voltages

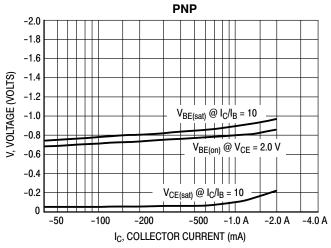


Figure 4. On Voltages

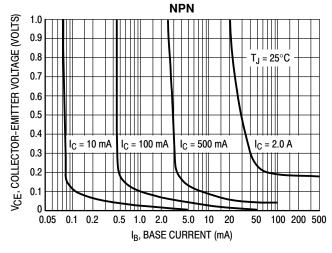


Figure 5. Collector Saturation Region

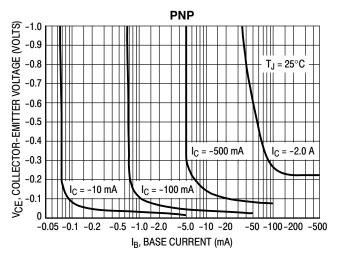
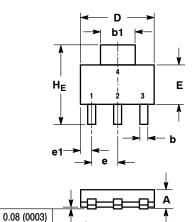


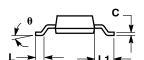
Figure 6. Collector Saturation Region

PZT751

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE N





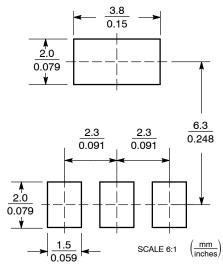
DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCH.

	CONTROLL	NG DIMENS	IIOIV. IIVOII.			
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20			0.008		
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	_	10°	0°	_	10°

STYLE 1: PIN 1. BASE

- 2. COLLECTOR 3. EMITTER
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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